# 2SC4154

FOR LOW FREQUENCY AMPLIFY APPLICATION SILICON NPN EPITAXIAL TYPE (Super mini type)

### **DESCRIPTION**

2SC4154 is a super mini package resin sealed silicon NPN epitaxial transistor,

It is designed for low frequency voltage application.

Complementary with ISA1602AM1.

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#### **FEATURE**

Small collector to emitter saturation voltage.

VCE(sat)=0.3V max(@lc=100mA,IB=10mA)

Excellent linearity of DC forward gain.

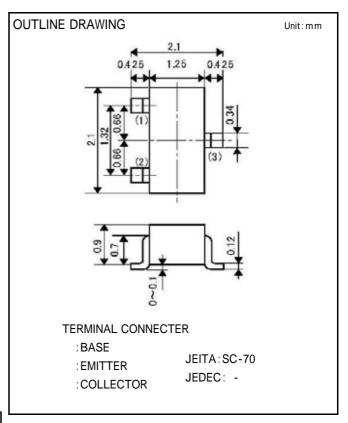
Super mini package for easy mounting

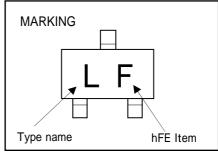
### **APPLICATION**

For Hybrid IC, small type machine low frequency voltage Amplify application.

## MAXIMUM RATINGS (Ta=25 )

Symbol	Parameter	Ratings	Unit
V <sub>CBO</sub>	Collector to Base voltage	50	V
$V_{CEO}$	Collector to Emitter voltage	50	V
$V_{EBO}$	Emitter to Base voltage	6	V
I <sub>o</sub>	Collector current	200	mA
P <sub>c</sub>	Collector dissipation	200	mW
T <sub>j</sub>	Junction temperature	+ 150	
T <sub>stg</sub>	Storage temperature	-55 ~ + 150	





## ELECTRICAL CHARACTERISTICS (Ta=25 )

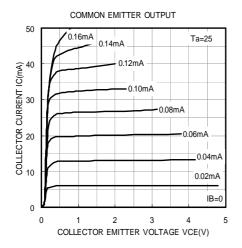
Parameter	Symbol Test conditions	Limits			Unit	
Farameter		rest conditions	Min	Тур	Max	Offic
C to E break down voltage	V(BR)CEO	I <sub>C</sub> =100 μ A ,R <sub>BE</sub> =	50	-	-	V
Collector cut off current	ICBO	V <sub>CB</sub> =50V, I <sub>E</sub> =0mA	-	-	0.1	μА
Emitter cut off current	IEBO	$V_{EB}$ =6V, $I_{C}$ =0mA	-	-	0.1	μА
DC forward current gain	hFE	$V_{CE}=6V, I_{C}=1mA$	150	-	500	
DC forward current gain	hFE	$V_{CE}$ =6V, $I_{C}$ =0.1mA	90	-	-	
C to E Saturation Voltage	VCE(sat)	I <sub>C</sub> =100mA ,I <sub>B</sub> =10mA	-	-	0.3	V
Gain bandwidth product	fT	V <sub>CE</sub> =6V, I <sub>E</sub> =-10mA	ı	200	-	MHz
Collector output capacitance	Cob	$V_{CB}=6V, I_{E}=0, f=1MHz$	1	2.5	-	pF
Noise figure	NF	V <sub>CE</sub> =6V, I <sub>E</sub> =-0.1mA,f=1kHz,RG=2k	-	-	15	dB

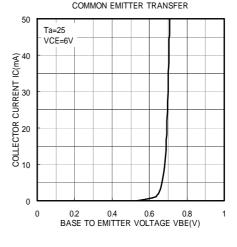
) It shows hFE classification at right table.

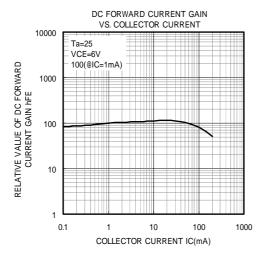
Item	Е	F
hFE Item	150 ~ 300	250 ~ 500

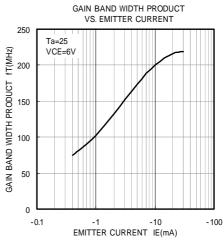
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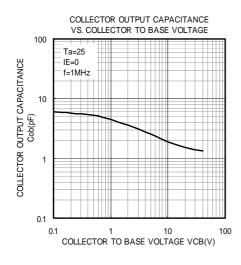
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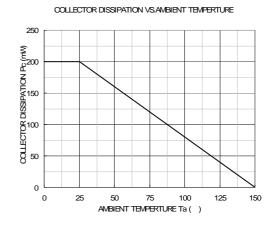






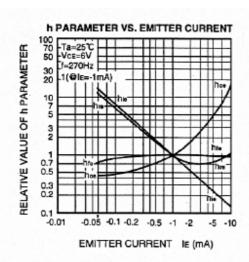


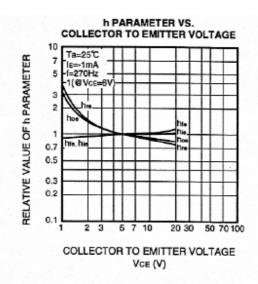




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### COMMON EMITTER h PARAMETER (TYPICAL VALUE)

Symbol	Parameter	Test conditions	Limits	Unit
hie	Closed loop small signal input impedance	Ta=25°C	8.5	kΩ
hre	Open loop small signal reverse voltage amplification factor	VCE=6V	0.1	×10-3
hte	Closed loop small signal forward current amplification factor	IE=-1mA	300	
hoe	Open loop small signal output admittance	1=270Hz	5.5	μS



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